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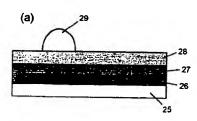
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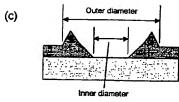
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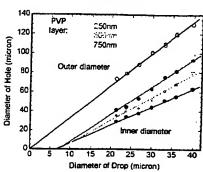
[Continued on next page]

(54) Title: FORMING INTERCONNECTS



(57) Abstract: A method for forming an electronic device, comprising: forming a first conductive or semiconductive layer; forming a sequence of at least one insulating layer and at least one semiconducting layer over the first conductive or semiconductive layer; locally depositing solvents at a localised region of the insulating layer so as to dissolve the sequence of insulating and semiconducting layers in the region to leave a void extending through the sequence of layers; and depositing conductive or semiconductive material in the void.





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patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM). European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR). OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

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According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols) IPC 7 H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

INSPEC, EPO-Internal

Category *	Citation of document, with Indication, where appropriate, of the relevant passages	Relevant to claim No.
X	WO 99 10939 A (KONINKL PHILIPS ELECTRONICS NV ;PHILIPS AB (SE)) 4 March 1999 (1999-03-04) the whole document	44-48
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Further documents are listed in the continuation of box C.	Patent family members are listed in annex.
Special categories of cited documents: "A" document defining the general state of the art which is not considered to be of particular relevance "E" earlier document but published on or after the international filing date "L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) "O" document referring to an oral disclosure, use, exhibition or other means "P" document published prior to the international filling date but later than the priority date claimed	T later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention "X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art. "A" document member of the same patent family
Date of the actual completion of the international search	Date of mailing of the international search report
19 February 2001	1 8. 05. 01
Name and mailing address of the ISA European Patent Office, P.B. 5818 Patentiaan 2 NL - 2280 HV Rijswijk Tel. (+31-70) 340-2040, Tx. 31 651 epo nl, Fax: (+31-70) 340-3018	Authorized officer Königstein, C

IN NATIONAL SEARCH REPORT

11	nal Application No	
PC1/G	B 00/04940	

	PC 1/GB 00/04940				
	(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT				
Category °	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.			
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A	EP 0 930 641 A (SEIKO EPSON CORP) 21 July 1999 (1999-07-21) the whole document	1			
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ational application No.
PCT/GB 00/04940

Box I	Observations where certain claims were found unsearchable (Continuation of item 1 of first sheet)
This Inte	ernational Search Report has not been established in respect of certain claims under Article 17(2)(a) for the following reasons:
1.	Claims Nos.: because they relate to subject matter not required to be searched by this Authority, namely:
2.	Claims Nos.: because they relate to parts of the International Application that do not comply with the prescribed requirements to such an extent that no meaningful International Search can be carried out, specifically:
з. [Claims Nos.: because they are dependent claims and are not drafted in accordance with the second and third sentences of Rule 6.4(a).
Box II	Observations where unity of invention is lacking (Continuation of item 2 of first sheet)
This Int	ternational Searching Authority found multiple inventions in this international application, as follows:
	see additional sheet
1.	As all required additional search fees were timely paid by the applicant, this International Search Report covers all searchable claims.
2.	As all searchable claims could be searched without effort justifying an additional fee, this Authority did not invite payment of any additional fee.
3.	As only some of the required additional search fees were timely paid by the applicant, this International Search Report covers only those claims for which fees were paid, specifically claims Nos.:
4. J	No required additional search fees were timely paid by the applicant. Consequently, this International Search Report is restricted to the invention first mentioned in the claims; it is covered by claims Nos.: 1-38,44-49
Rema	The additional search fees were accompanied by the applicant's protest. No protest accompanied the payment of additional search fees.

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FURTHER INFORMATION CONTINUED FROM PCT/ISA/ 210

This International Searching Authority found multiple (groups of) inventions in this international application, as follows:

1. Claims: 1-38,44-49

Patterning of organic insulating layers by selective etching

The prior Art describes a field effect transistor substantially consisting of organic materials.

The new features mentioned in claims 1-38 are contact holes, made in organic dielectric layers by wet etching using an ink-jet printing system to locally suply the etch liquid.

From this we can formulate an objective problem of making contact holes in organic dielectric layers by wet etching using an ink-jet printing system to locally suply the etch liquid.

The special technical features, as defined in Rule 13(2) PCT, are contact holes, made in organic dielectric layers by wet etching using an ink-jet printing system to locally suply the etch liquid.

2. Claims: 39-43

Selective doping of organic insulating layers

The prior Art describes a field effect transistor substantially consisting of organic materials.

The new features mentioned in claims 1-38 are conductive (interconnection) patterns made by selective doping organic insulating layers to make them conductive. The dopants are applied using an ink-jet printing system.

From this we can formulate an objective problem of making conductive patterns made by selective doping organic insulating layers to make them conductive, applying the dopants are using an ink-jet printing system.

The special technical features, as defined in Rule 13(2) PCT, are conductive (interconnection) patterns made by selective doping organic insulating layers to make them conductive. The dopants are applied using an ink-jet printing system.

INTEGRATIONAL SEARCH REPORT

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